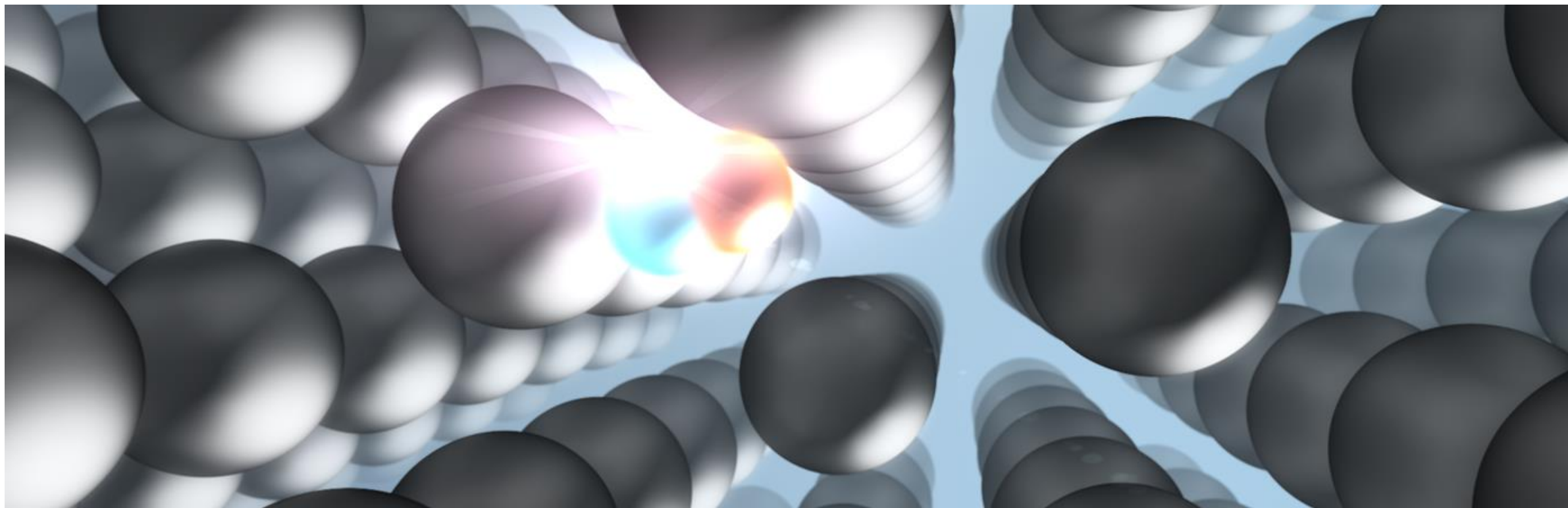




11th International Workshop on Thin Films and New Ideas for  
Pushing the Limits of RF Superconductivity - TFSRF2024



# Positron annihilation spectroscopy: pursuing point defects in superconducting film

Institute of Radiation Physics · Department of Nuclear Physics · Sebastian Klug · [s.klug@hzdr.de](mailto:s.klug@hzdr.de) · [www.hzdr.de](http://www.hzdr.de)



# Introduction

## M. Sc. Sebastian Klug

- Doctoral Student since May 2024
- HZDR, Institute of Radiation Physics
  - topics: Positron Annihilation Spectroscopy (PAS), SRF cavities, Magnetron Sputtering (DC-/HiPIMS)

## Ph.D. project

- role of **defects & defect development** in superconducting thin films
  - impact on superconducting properties
- defects/voids/interfaces created **during** thin film creation
  - **in-situ investigations** of defect dynamics with **PAS**
  - materials: **Nb, NbN, NbTiN, Nb<sub>3</sub>Sn**
  - study of **multilayer thin films** (SIS structure)

# Introduction

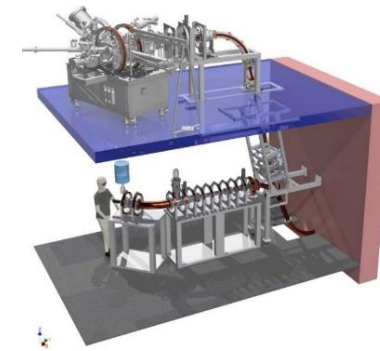
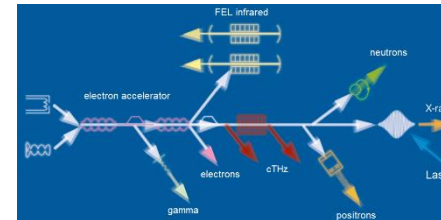
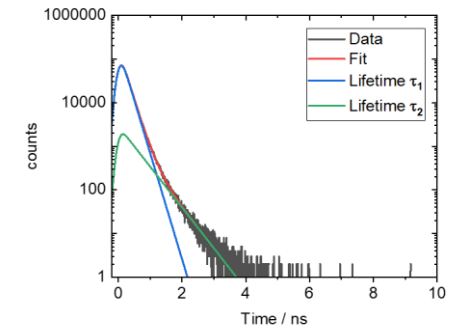
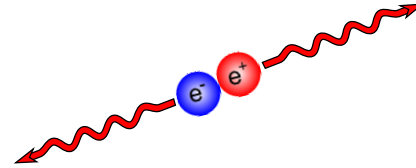
## NOVALIS project (Novel accelerator technology for efficient light sources)

- German research project (Federal Ministry of Education and Research of Germany)
- Consortium of different German research institutions:
  - Technical University of Darmstadt (TUDA)
  - University of Hamburg (UHH)
  - University of Siegen (USI)
  - Helmholtz-Zentrum Berlin (HZB)
  - University of Wuppertal (BUW)
  - **Helmholtz-Zentrum Dresden-Rossendorf (HZDR)**
- **AIM: significant reducing of operational power losses of SRF cavities**
  - **Beyond Niobium** research, focus on thin films
    - task of HZDR: providing facilities for **positron annihilation spectroscopy** of thin film samples



# Outline

- **Positron Annihilation Spectroscopy**
- **Recent research of point defects**
- **Positron facilities at HZDR**
- **Outlook: Magnetron Sputtering & in-situ PALS**
- **Conclusion**



# Positron Annihilation Spectroscopy (PAS)

Positron / DBS / PALS

# Positron Annihilation Spectroscopy (PAS)

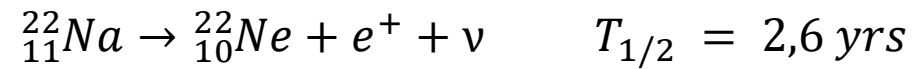
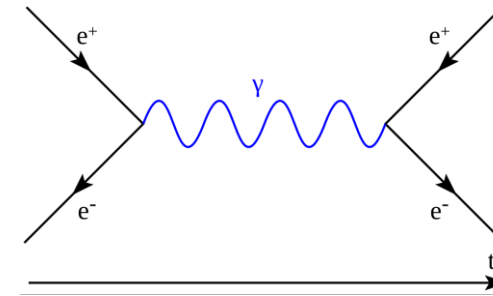
## Positron

### anti-particle of electron

- same mass, opposite charge
- annihilation with characteristic radiation (**511 keV**)

### positron generation

- natural source →  **$\beta^+$  decay**
- artificial creation → **pair production**



with photons or bremsstrahlung

# Positron Annihilation Spectroscopy (PAS)

## Positron

### Interaction mechanism positron ( $e^+$ ) $\leftrightarrow$ matter

#### 1) Generation & implantation of $e^+$

- dependence on implantation energy

#### 2) Thermalization

- $<10$  ps
- losing of kinetic energy

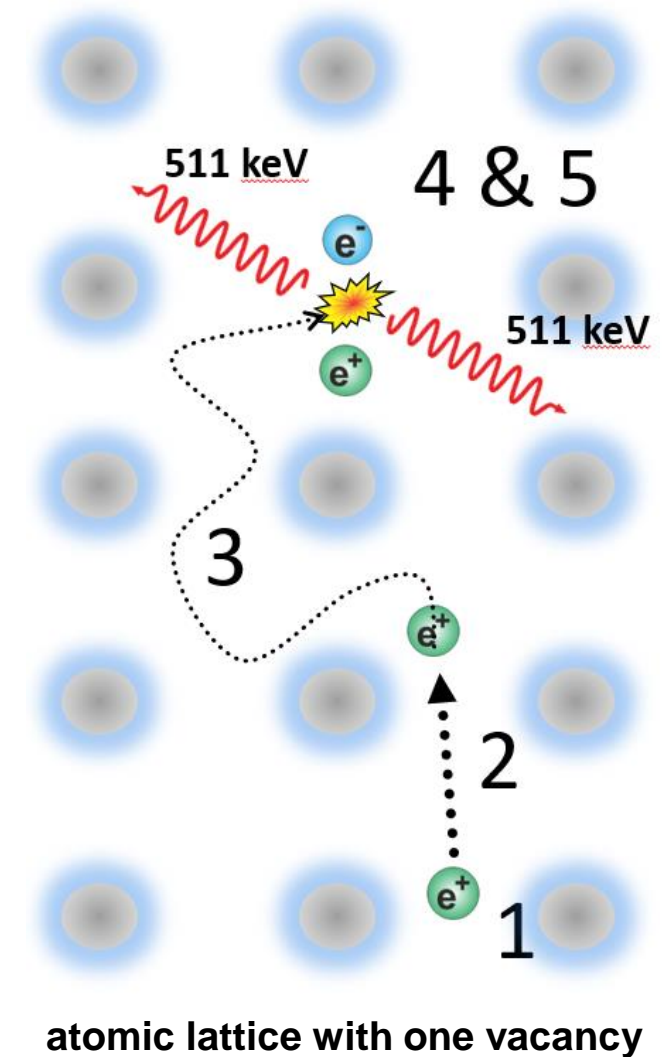
#### 3) Diffusion through the lattice

- 100 ps, up to 100 nm

#### 4) Trapping in defects

- different electron densities

#### 5) Annihilation with electron & Emission of photons



# Positron Annihilation Spectroscopy (PAS)

## Positron

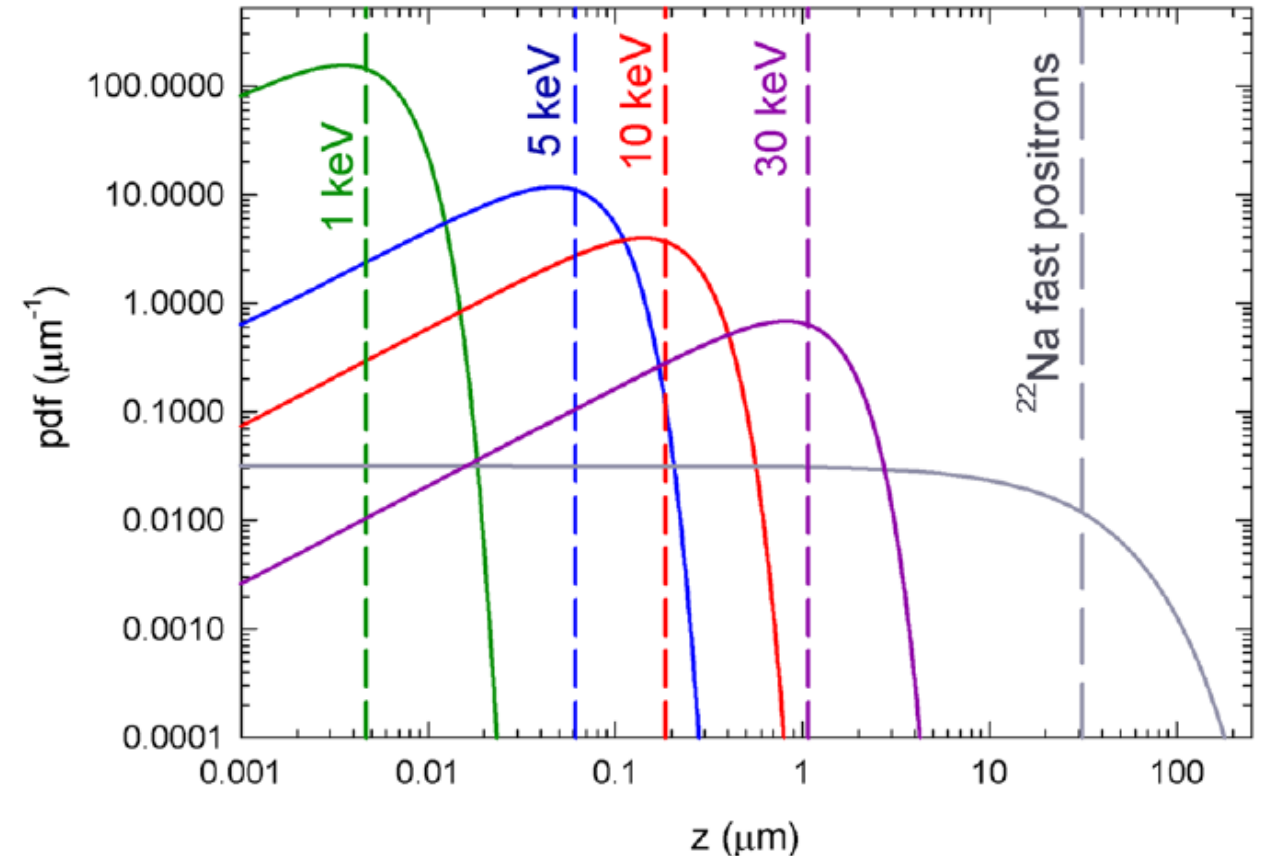
### Implantation (Makhov) profile

- mean positron penetration depth  $\langle z \rangle$

$$\langle z \rangle [\text{nm}] = \frac{36}{\rho [\text{gcm}^{-3}]} E_p^{1.62} [\text{keV}]$$

- dependent on  $E_p$  and  $\rho$
- **low** implantation energy  $E_p$ 
  - surface-near implantation
  - sharp profile
- **high** implantation energy  $E_p$ 
  - deeper implantation
  - broadening of profile (positron scattering)

- Optimal thickness of examination: **50 - 300 nm**



### Makhov profile for Nb

Wenskat, M. et al. Scientific Reports 10(2020), 8300

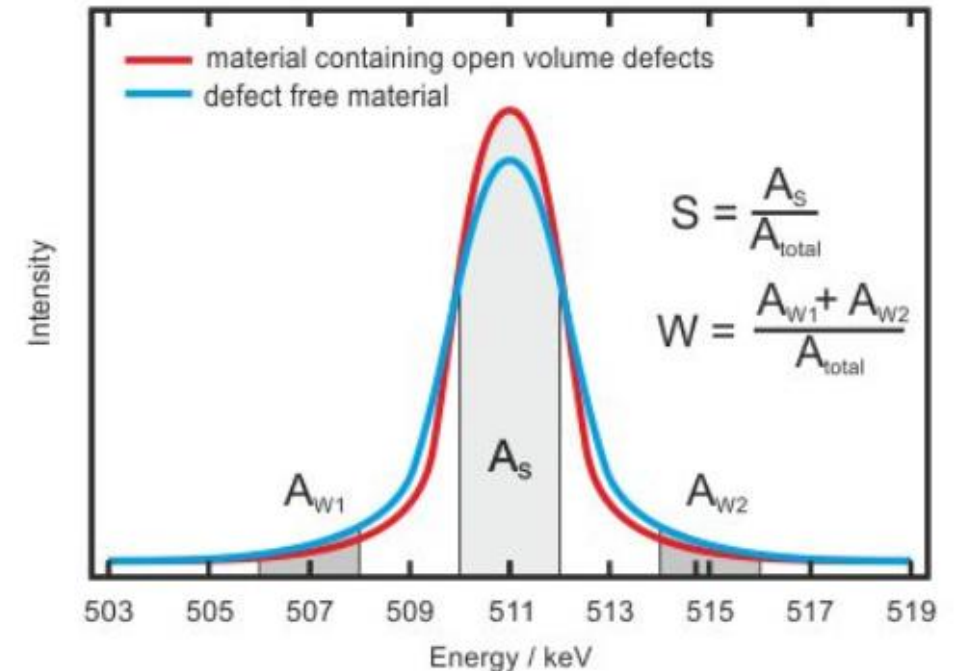


# Positron Annihilation Spectroscopy (PAS)

## Doppler-Broadening Spectroscopy (DBS)

### Doppler broadening of annihilation line (511 keV)

- electron momentum → energy shift
- different fractions of electrons
- **low electron momentum** (valence electrons)
  - **S** (shape) parameter → **defect concentration**
- **high electron momentum** (core electrons)
  - **W** (wing) parameter → **atomic environment** of defects



annihilation line with **S** and **W** parameters

# Positron Annihilation Spectroscopy (PAS)

## Positron Annihilation Lifetime Spectroscopy (PALS)

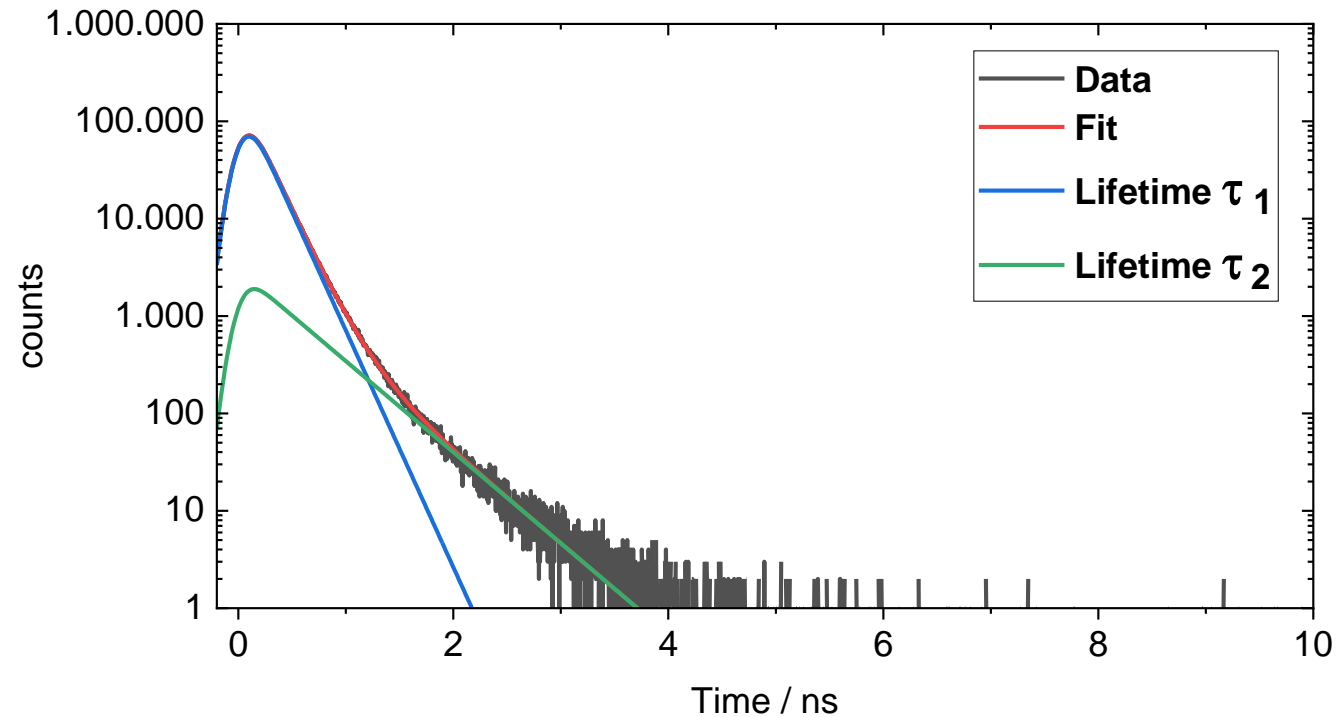
### Lifetime of positrons

- time between generation and annihilation of positrons

### Spectrum of positron lifetime

- **nonlinear** fitting process required
- convolution with **time resolution function**
- exponential decay terms ( $i \in \mathbb{N}$ )
  - **lifetime components**  $\tau_i$  (defect size)
  - **intensity**  $I_i$  (defect density)

$$N(t) = \sum_{i=1}^{k+1} \frac{I_i}{\tau_i} \exp\left(-\frac{t}{\tau_i}\right)$$

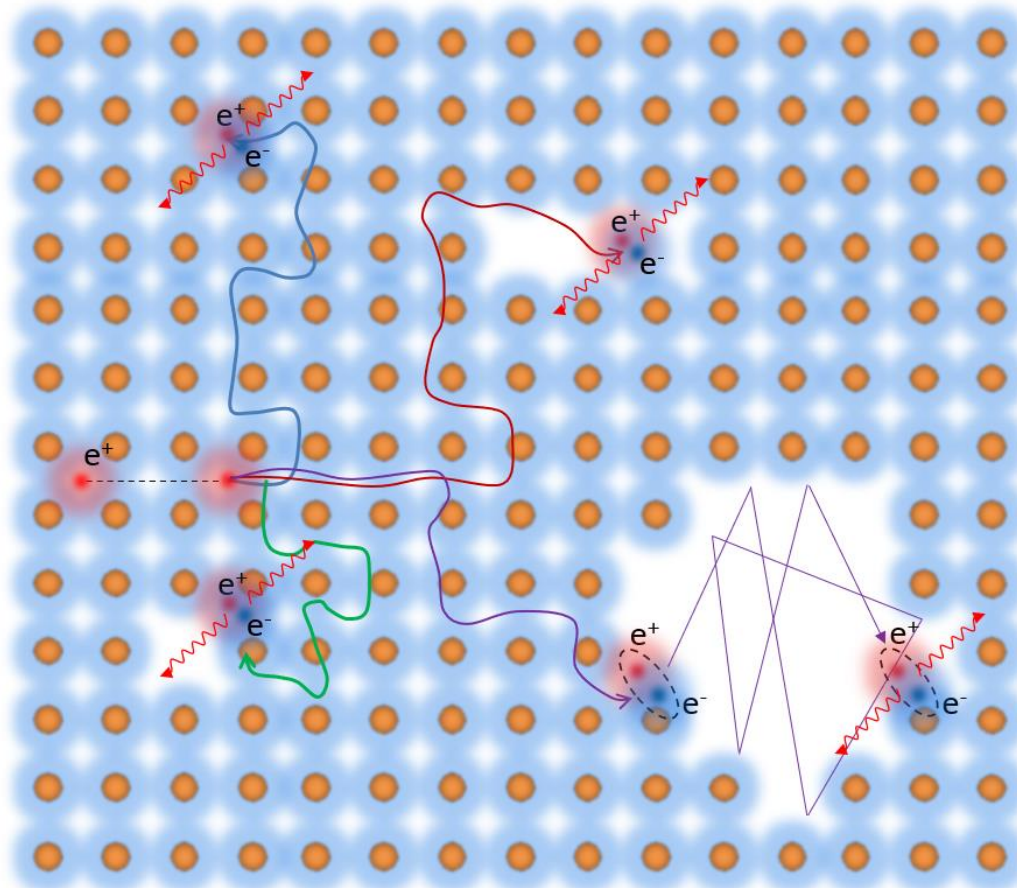
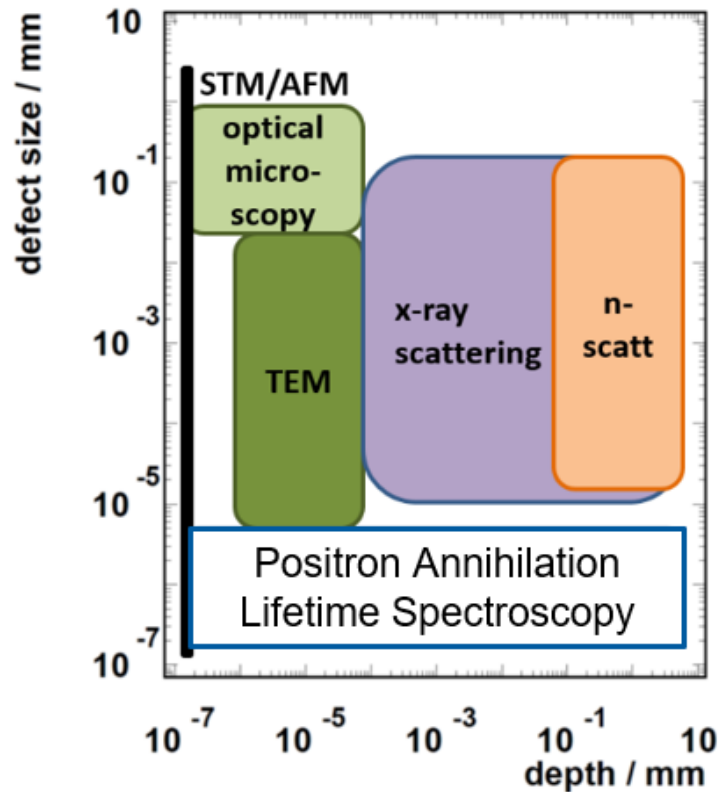


2 component fit for Nb sample (6 keV implantation energy)

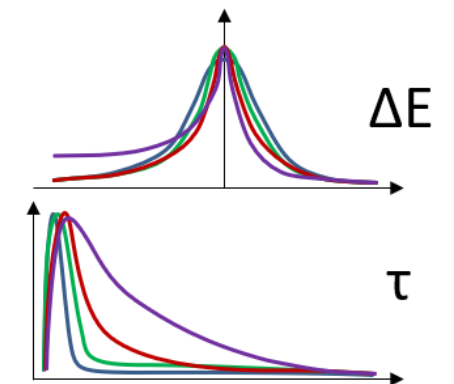
# Positron Annihilation Spectroscopy (PAS)

## Positron Annihilation Lifetime Spectroscopy (PALS)

Non-destructive and high-sensitivity to small defects (atomic scale)



- bulk
- mono-vacancy
- vacancy agglomeration
- void / pore



# Recent research of point defects

Vacancy kinetics in Nb / Point defects of Nb-based thin films

# Vacancy kinetics in Nb

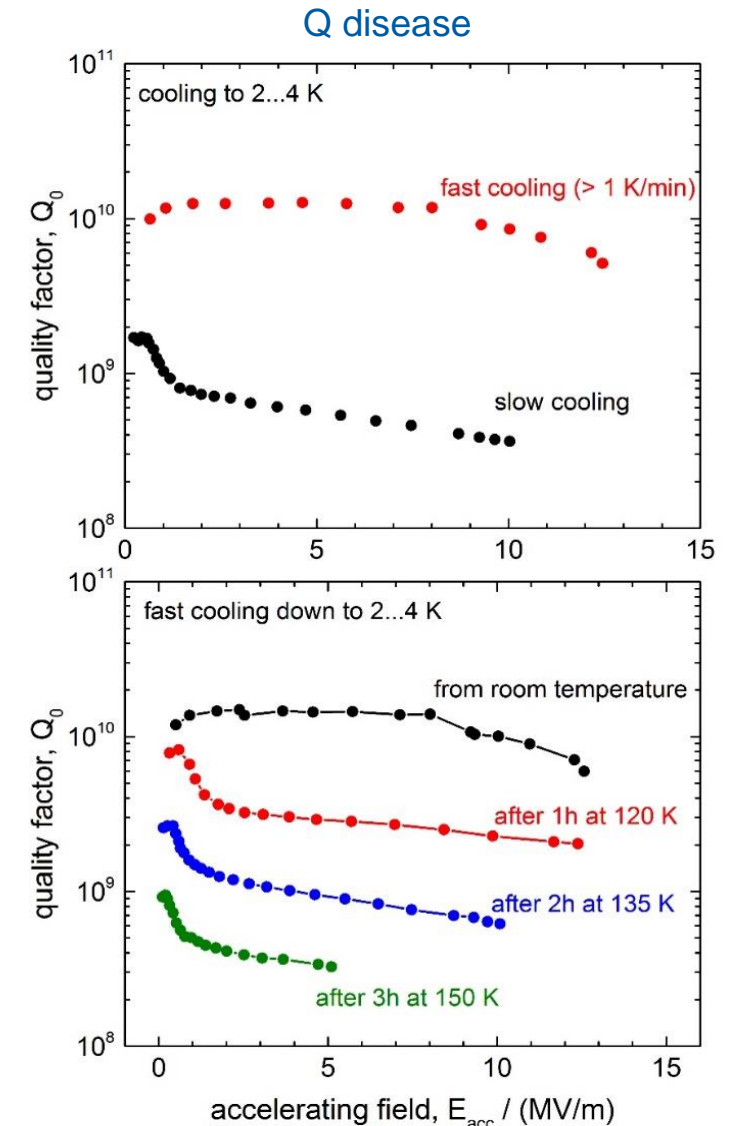
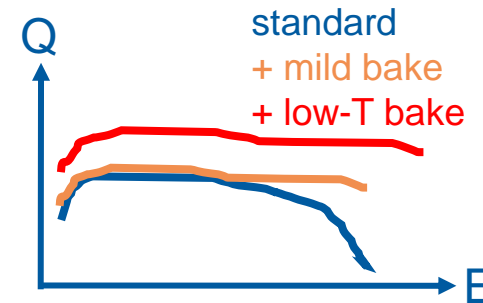
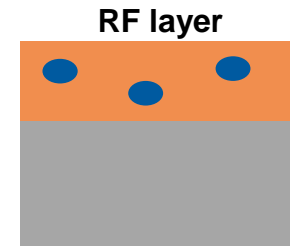
Collaboration with M. Wenskat (DESY, DE) & J. Čížek (Prague, CZ)

## Origin of Q disease

- formation of **niobium hydrides** in the rf surface layer during cooling down
- **open volume lattice defects** have high trapping potential for impurities, especially hydrogen: **vacancy-hydrogen complexes**

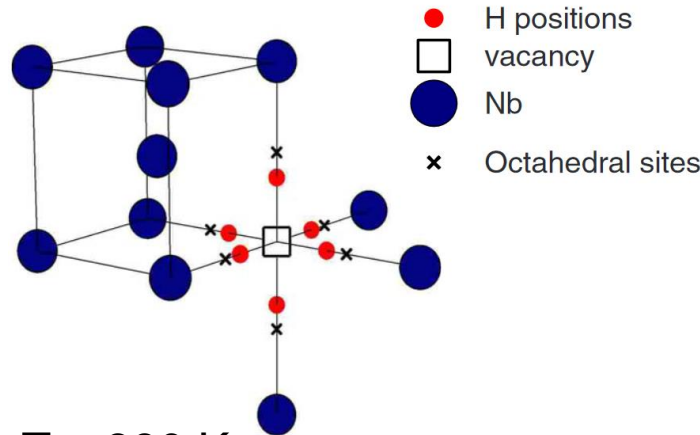
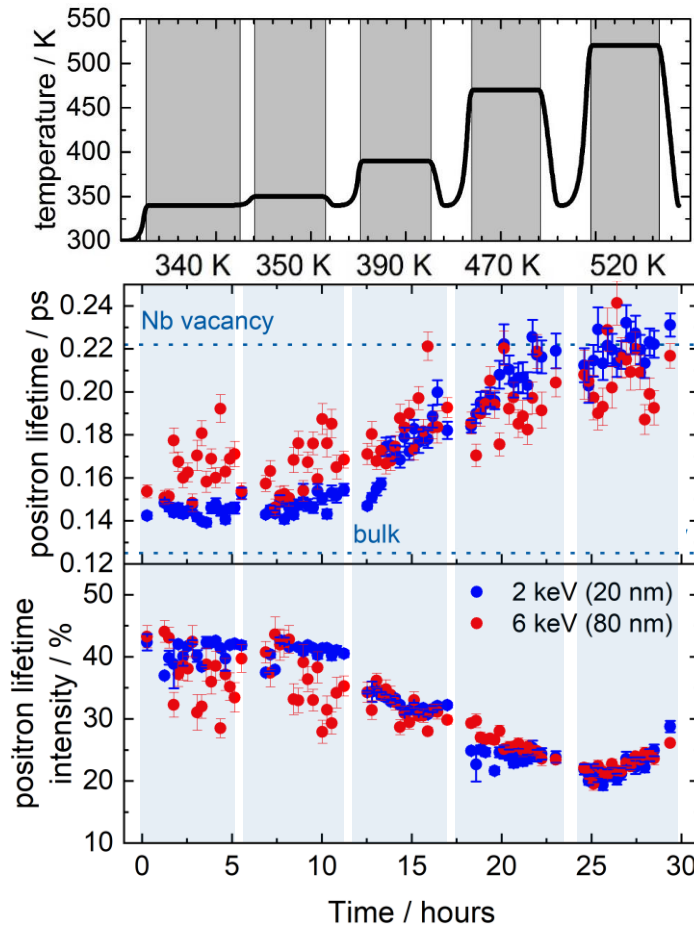
## Curing Q disease

- **mild bake**: at 390 K for 48 h ( $< 1e-6$  mbar) to avoid high-field Q slope (accidentally found!)
- **low-T bake**: only 350 K for first 2 h  
Q losses reduced by factor 2  
increased achievable accelerating field by  $>10\%$

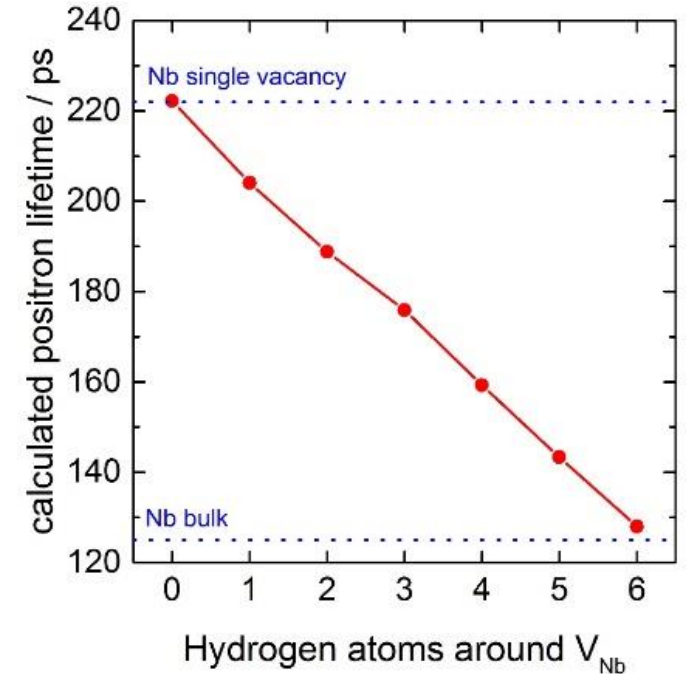


# Vacancy kinetics in Nb

Collaboration with M. Wenskat (DESY, DE) & J. Čížek (Prague, CZ)



- T = 390 K:  
shows most significant changes (already after short times)
- T > 390 K:  
hydrogen released from complexes (lifetime increases)  
v+nH concentration decreases (intensities decrease)



Wenskat, M. et al. Phys. Rev. B 106(2022), 094516  
 Wenskat, M. et al. Scientific Reports 10(2020), 8300

# Point defects of Nb-based thin films

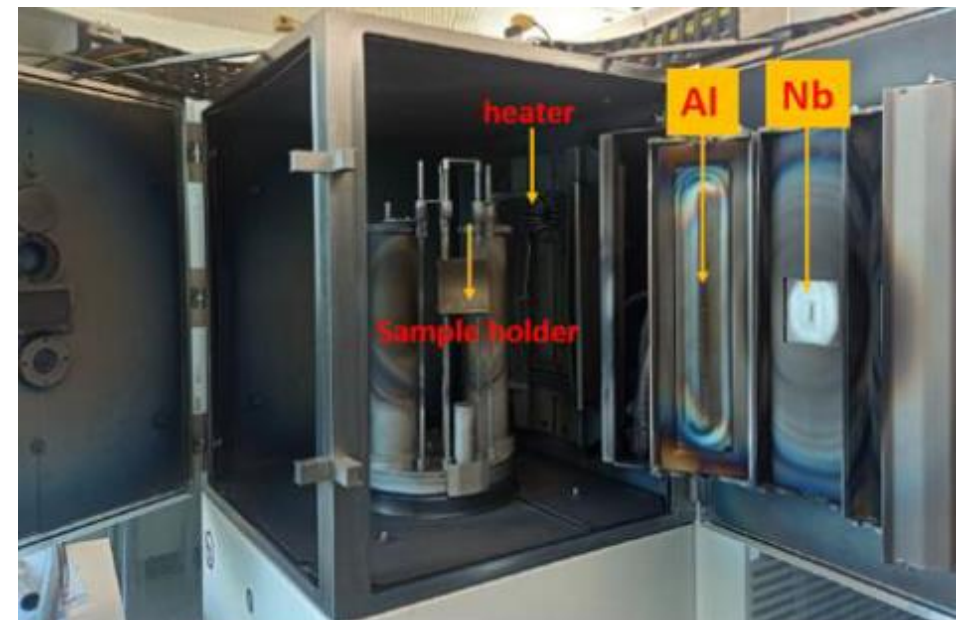
## Magnetron sputtering

### Thin film creation

- cooperation with **University of Siegen, Germany**
  - Prof. Dr. rer. nat. habil. Xin Jiang & Dr. Aleksandr Zubtsovskii
  - NOVALIS project
- **knowledge transfer** for new sputtering chamber @HZDR
- **reference samples** for future sample series

### Sample characterization @HZDR, Germany

- XRD ( $\theta - 2\theta$  scan)
- DBS & PALS

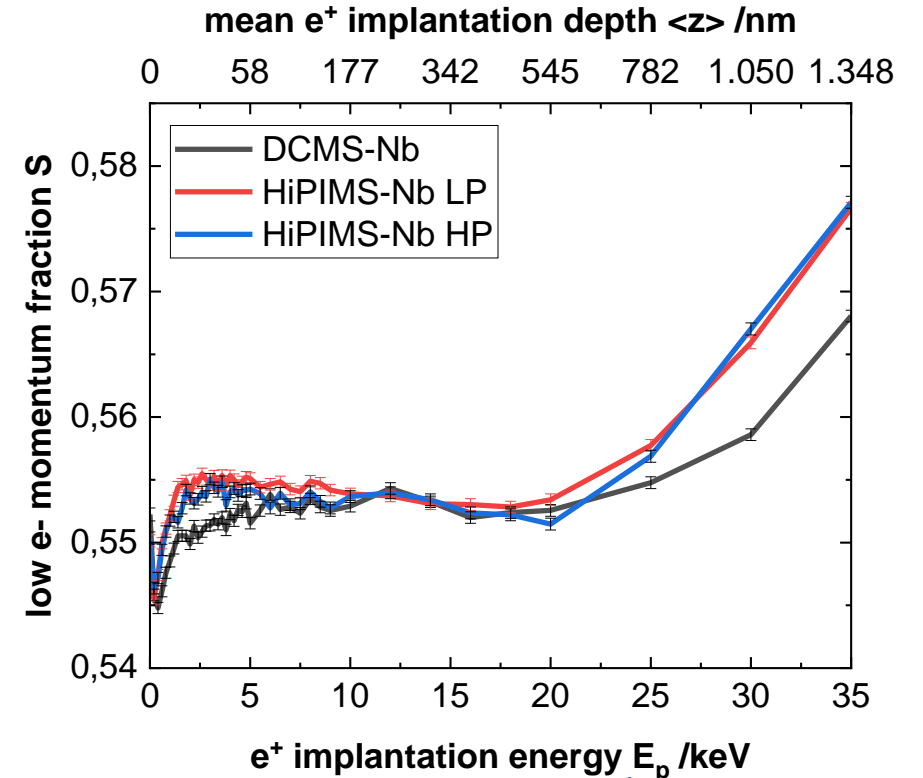
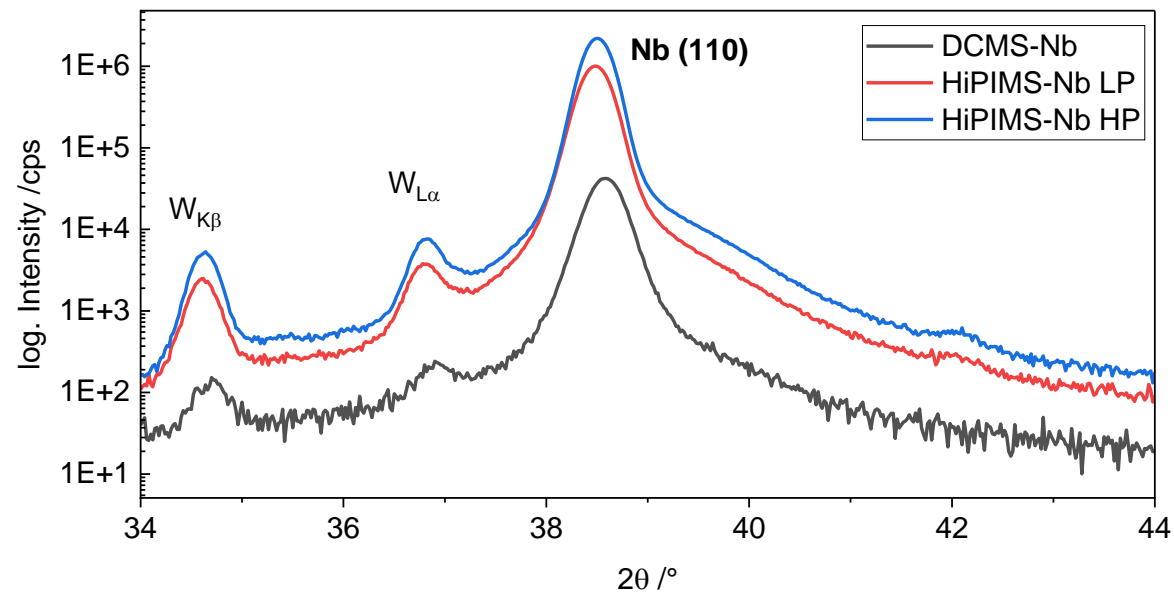


CemeCon CC800 at University of Siegen

# Point defects of Nb-based thin films

Nb films on Si(100)

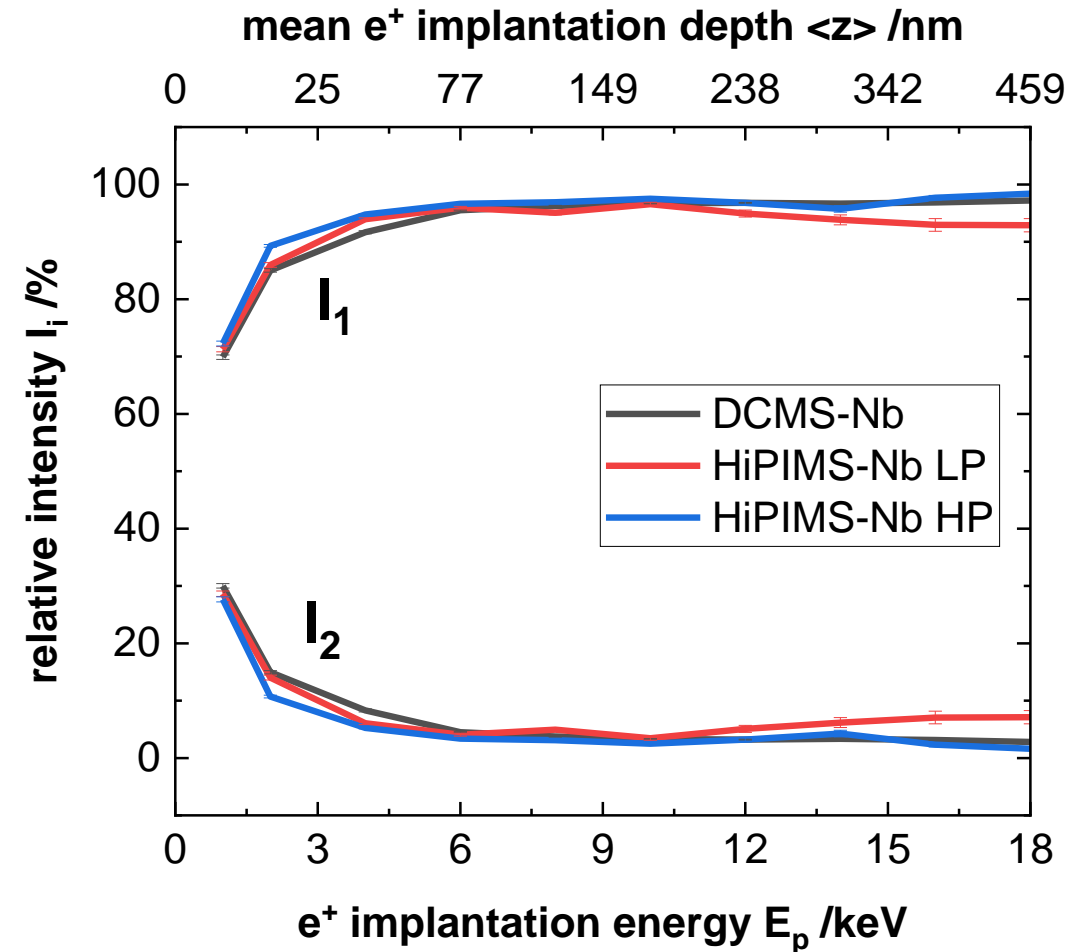
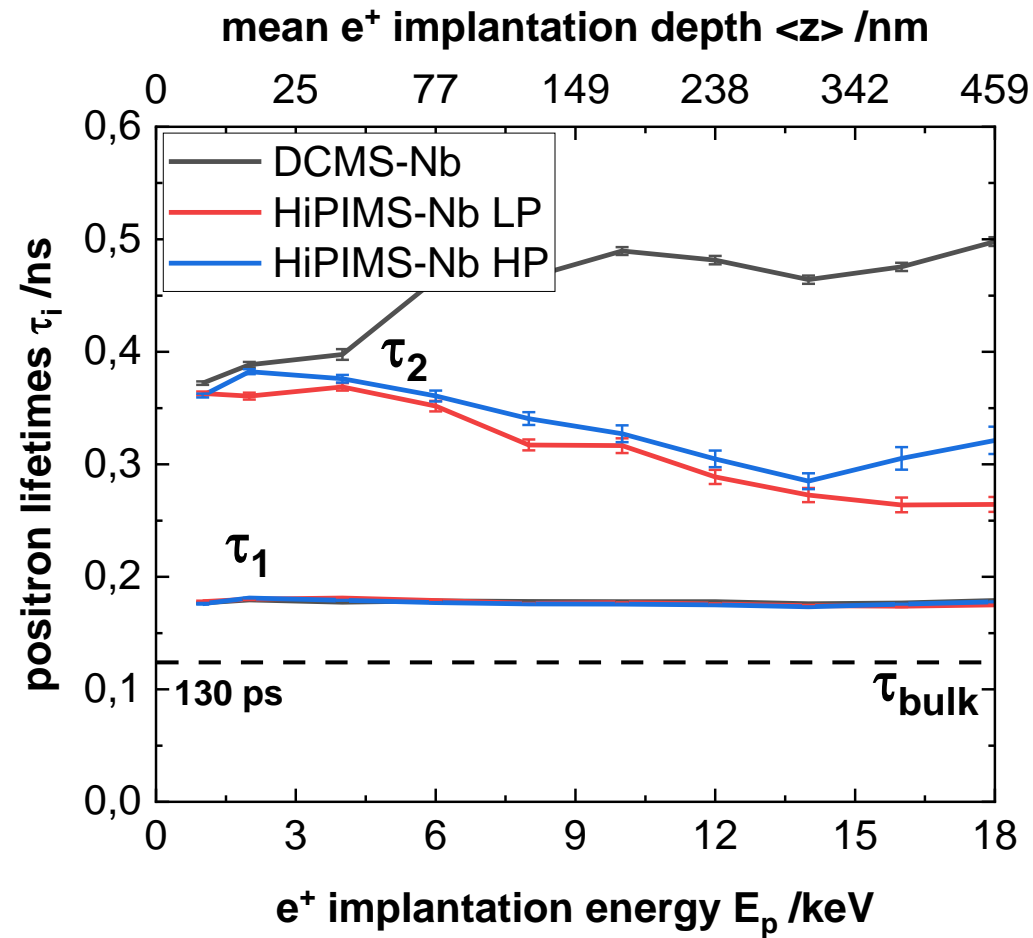
sample	cathode type	Power (W/cm <sup>2</sup> )	p_gas (mbar)	Ar flow (sccm)	N2 flow (sccm)
DCMS-Nb	DC	4,54	0,00801	410,0	0,0
HiPIMS-Nb LP	HiPIMS	4,54	0,00801	500,0	0,0
HiPIMS-Nb HP	HiPIMS	6,82	0,02001	700,0	0,0





# Point defects of Nb-based thin films

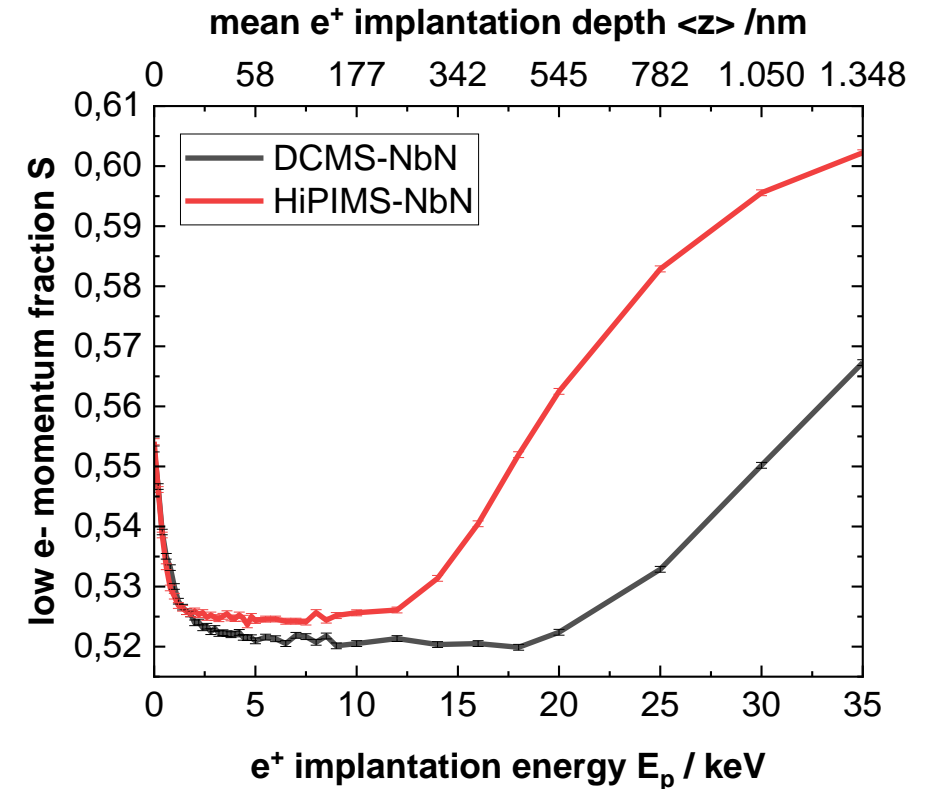
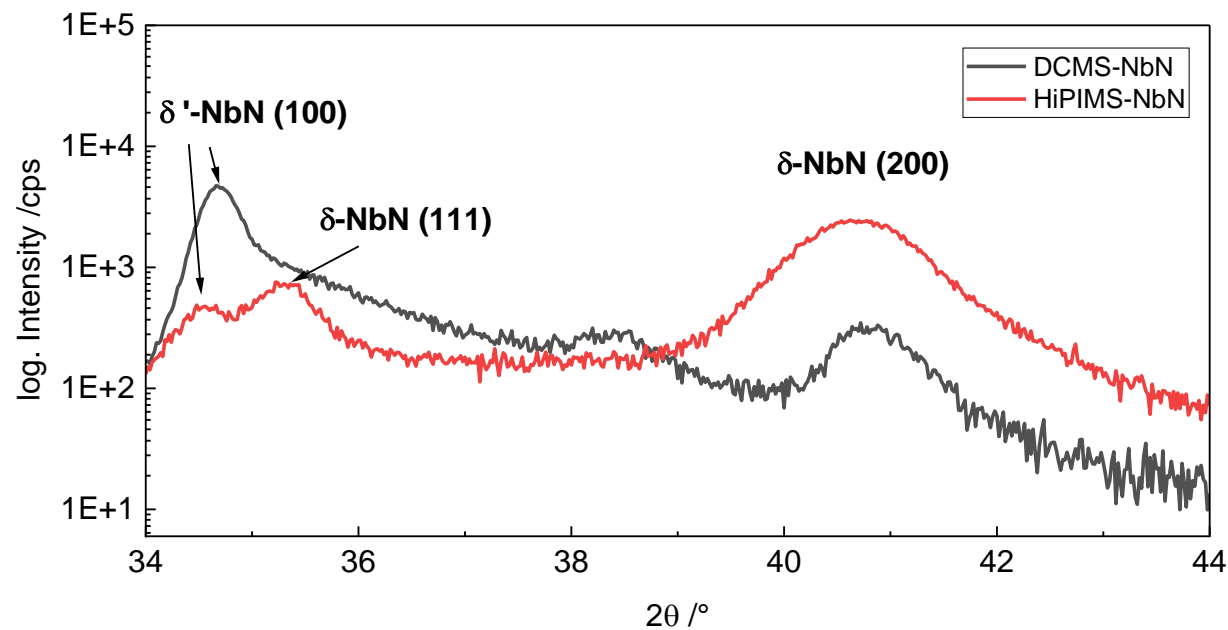
Nb films on Si(100)



# Point defects of Nb-based thin films

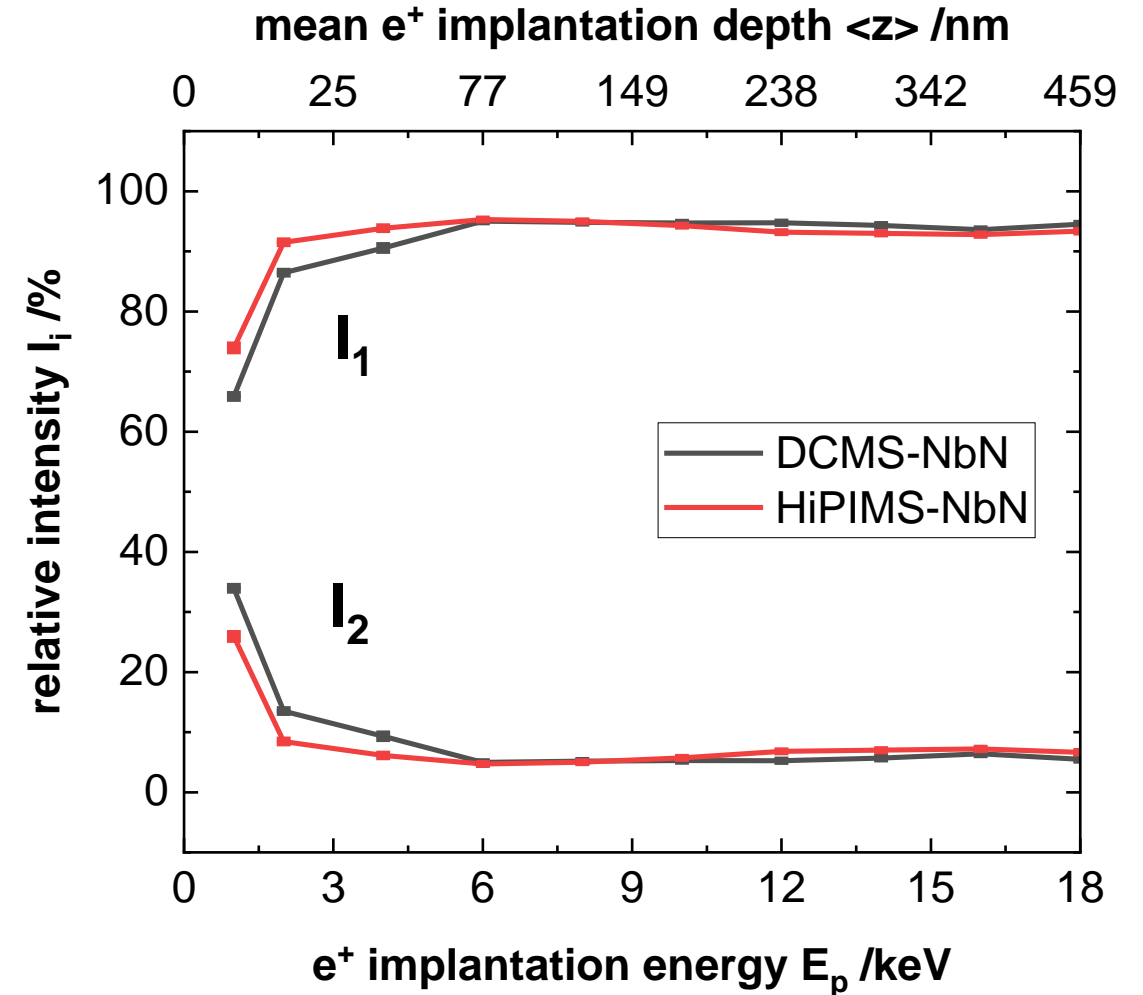
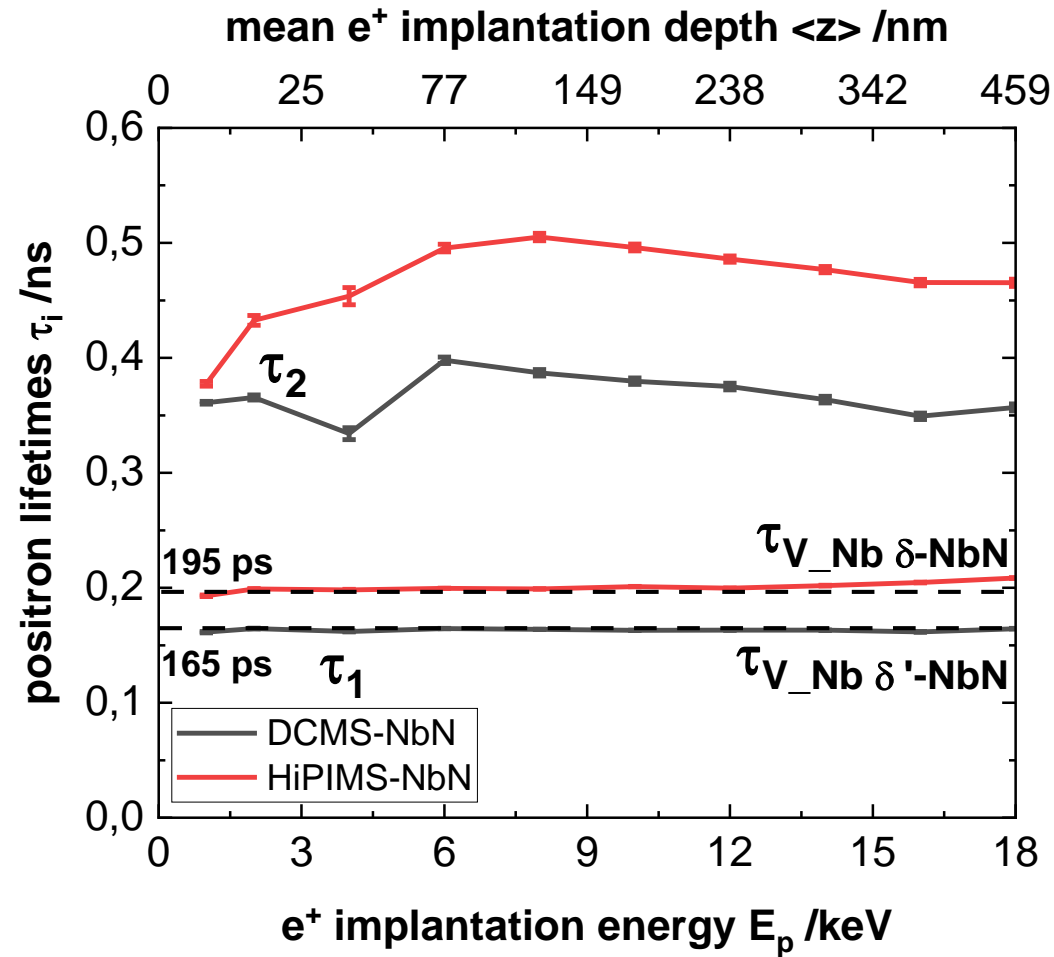
NbN films on Si(100)

sample	cathode type	Power (W/cm <sup>2</sup> )	p_gas (mbar)	Ar flow (sccm)	N2 flow (sccm)
DCMS-NbN	DC	5,68	0,01315	522,5	45,5
HiPIMS-NbN	HiPIMS	4,54	0,02291	641,8	71,3



# Point defects of Nb-based thin films

NbN films on Si(100)



# Positron user facilities at the HZDR

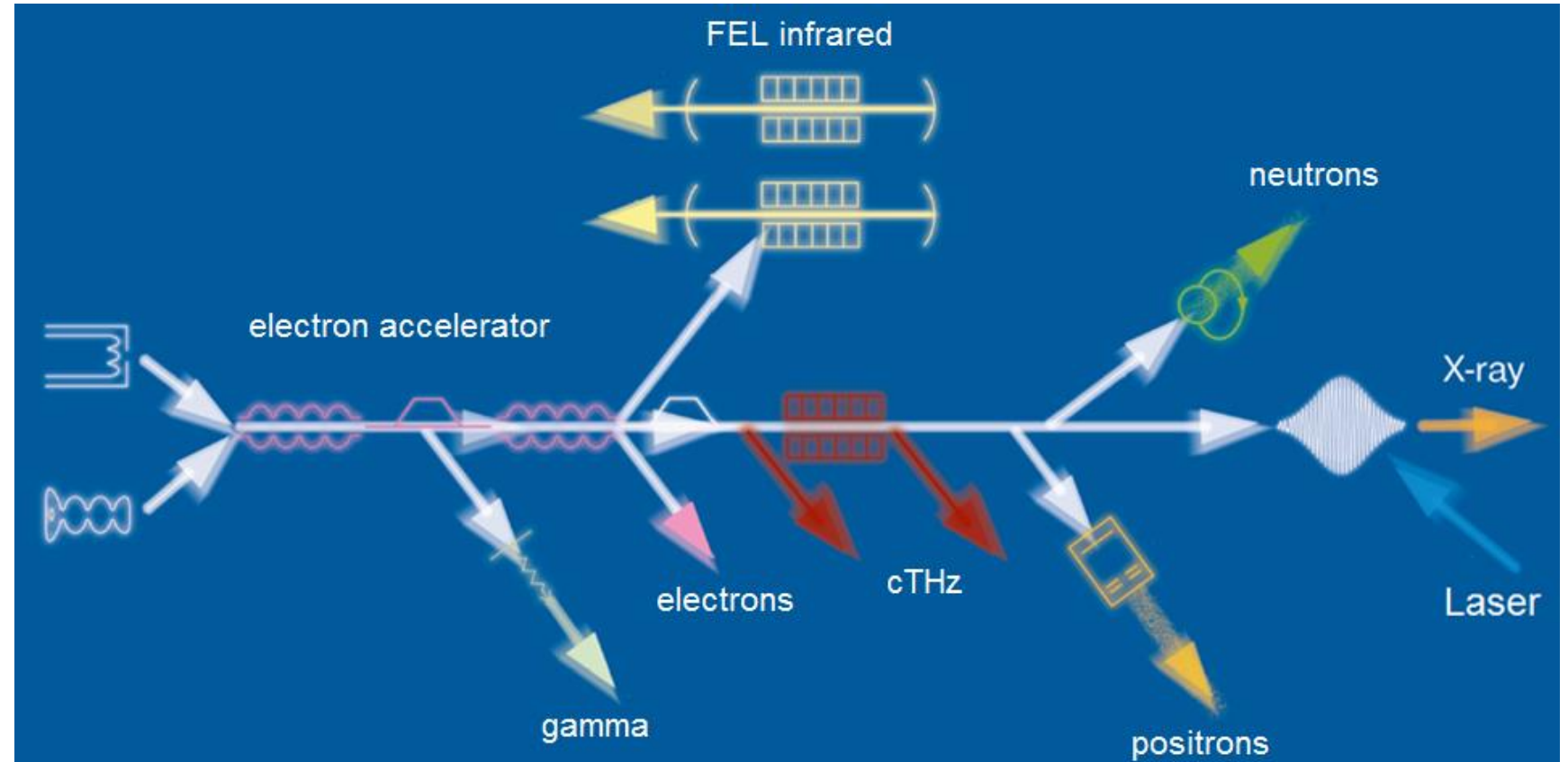
ELBE / SPONSOR / MePS / Access for user

# Positron user facilities at the HZDR

ELBE (Electron Linear accelerator with high Brilliance and low Emittance)

## ELBE as User Facility

- > 50 % of beamtime for **external user groups**



# Positron user facilities at the HZDR

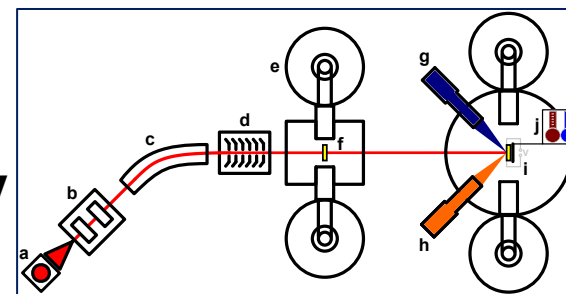
## SPONSOR (The Slow-Positron System of Rossendorf)

### Usage of $^{22}\text{Na}$ source

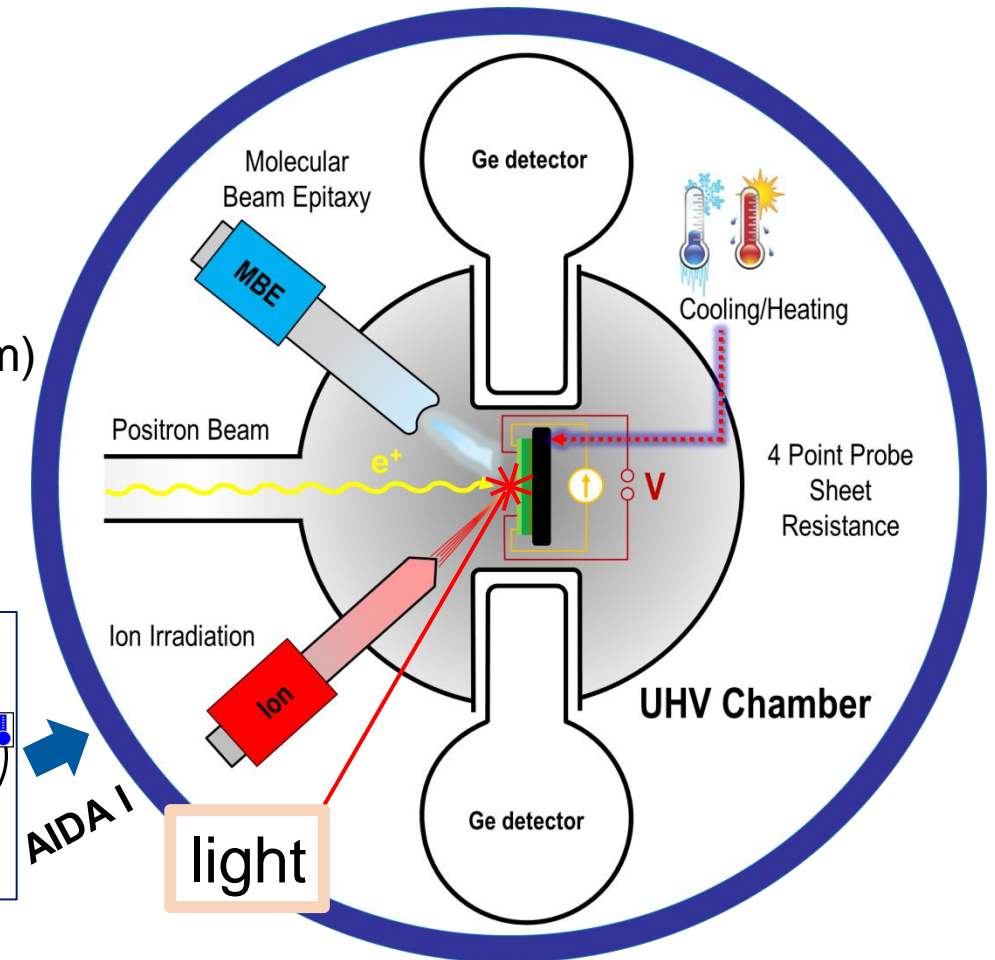
- **DBS** (defect size, density and chemistry)
- **depth resolved** measurements
- implantation energy ( $E_p$ ) **0...35 keV** (depth ~20 nm to few  $\mu\text{m}$ )

### Apparatus for in-situ defect analysis (AIDA I)

- base pressure:  **$2\text{e-}9$  mbar**
- temperature: **100 - 1200 K**
- Molecular Beam Epitaxy (**MBE**)
- ion irradiation:  $E_{\text{ion}} = \mathbf{0,5...5,0}$  keV
- sheet resistance (**4 point probe**)
- sample bias ( **$\pm 1000$  V**)



SPONSOR

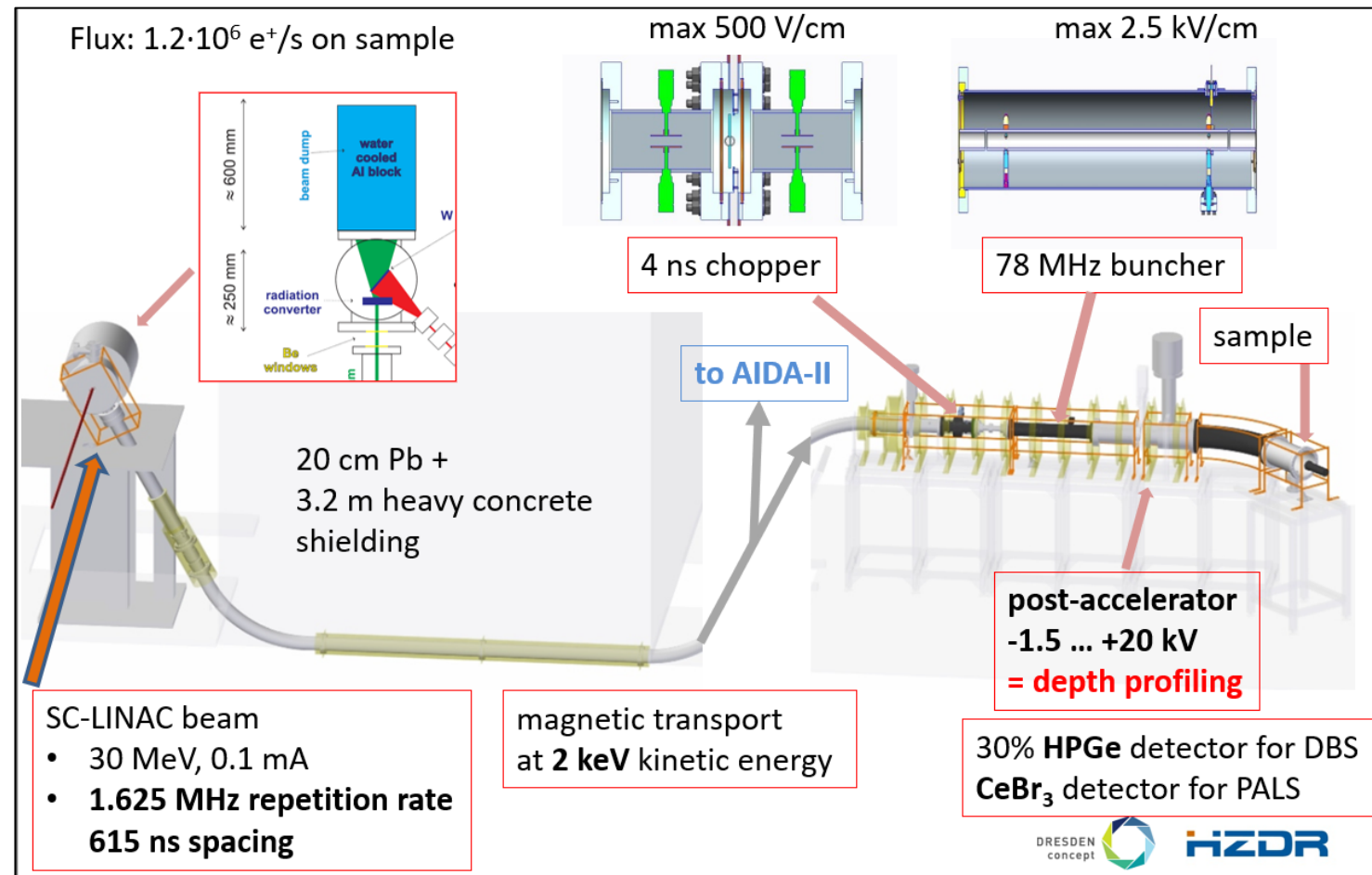


# Positron user facilities at the HZDR

## MePS (Mono-energetic Positron Spectroscopy)

### Usage of Linac

- **PALS** (defect size and density)
- **depth resolved** measurements
- implantation energy ( $E_p$ ) **0...18 keV**
- temperature **up to 800 K**
- planned implantation of cryostat (**20 K**)



# Positron user facilities at the HZDR

Access for user

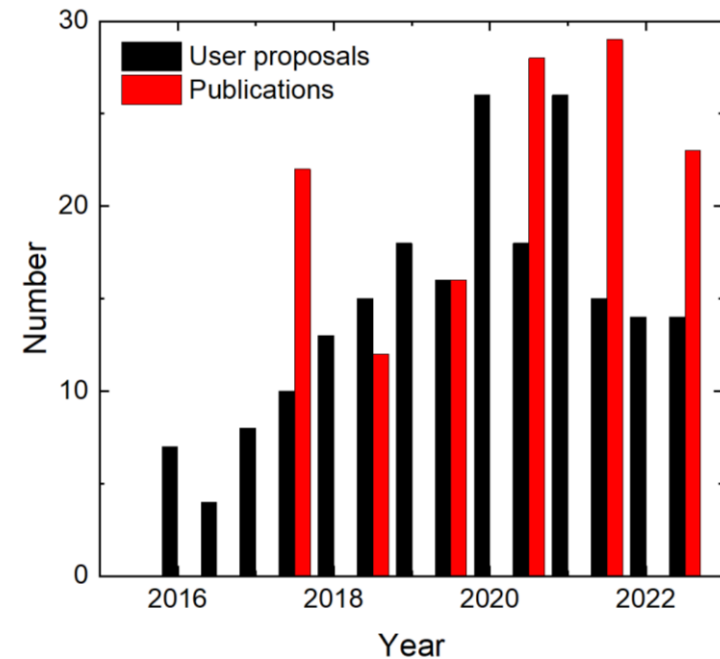
## Application with scientific user proposal

- submitted through the user portal **GATE**
- evaluation by international and interdisciplinary Scientific Advisory Committee
- free of charge for all non-proprietary research

- Website <https://www.hzdr.de/db/Cms?pNid=1732>

## Deadline

- twice a year
- next call for 1<sup>st</sup> half 2025:
  - **September 23rd, 2024** (already next Monday!)



~ 30 proposals / year



# Outlook: Magnetron Sputtering & in-situ PALS

AIDA II / future plans

# Outlook: Magnetron Sputtering & in-situ PALS

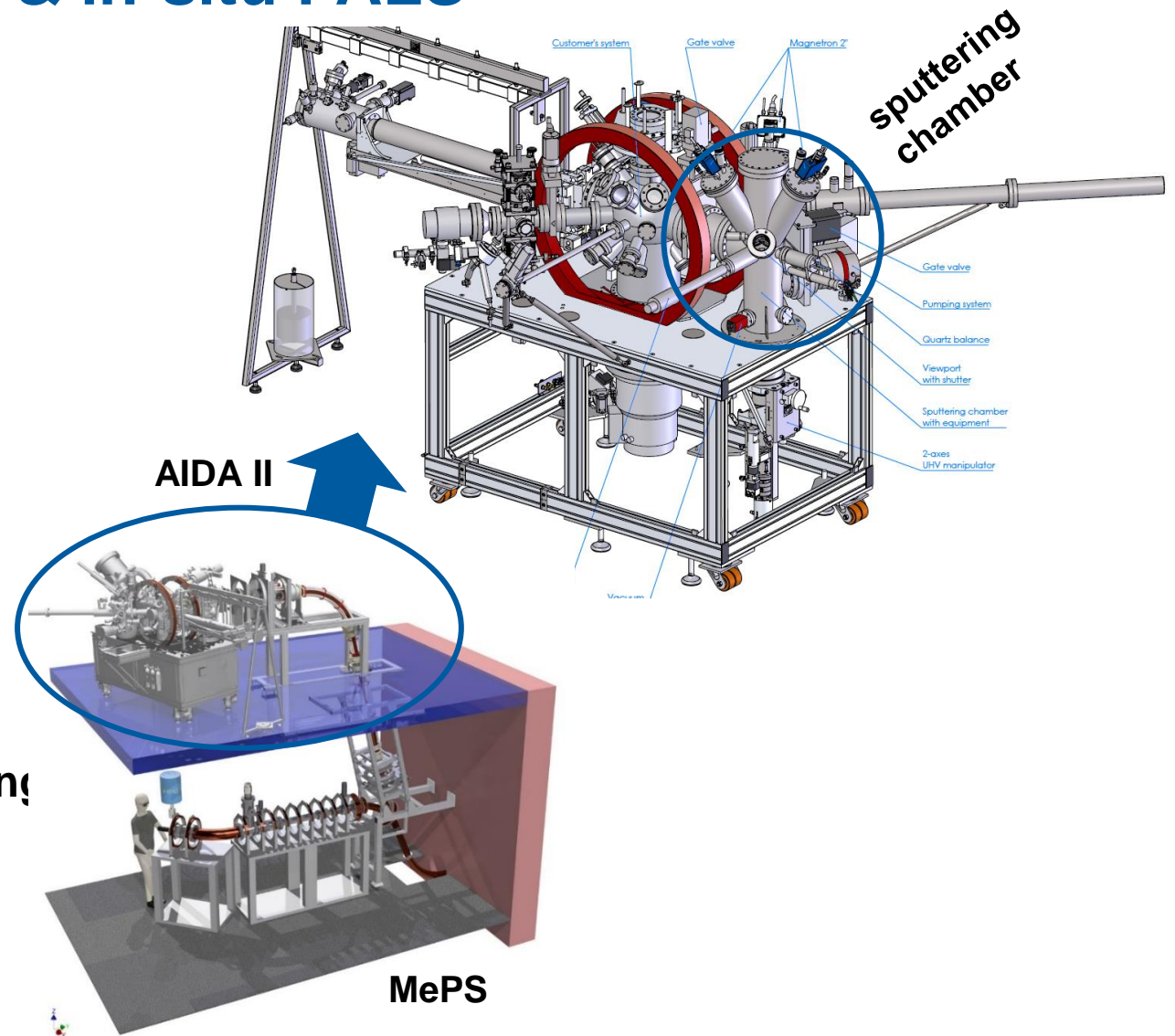
## AIDA II

### Magnetron sputter chamber

- 3 confocal magnetrons: 2x DC, 1x RF; 400 W
- working gases: Ar, N<sub>2</sub>, O<sub>2</sub>
- **2-inch** targets
- base pressure < 1e-9 mbar
- temperature range -180 to 800 °C

### In-situ characterization (PALS)

- Apparatus for in-situ defect analysis (**AIDA II**)
- combination of **MePS** and magnetron sputtering
- novelty: **PALS during sputtering process**
  - tracking of development of point defects



# Outlook: Magnetron Sputtering & in-situ PALS

future plans

## next steps

- finishing work on **AIDA II**
- investigations of **influence of magnetron sputtering process parameters**
- in-situ PALS of **Nb** and **NbN** thin films
- ex-situ characterization with **XRD, SEM, AFM**
- characterization of **superconducting properties**

## later

- Study of **NbTiN, Nb<sub>3</sub>Sn** and final aim of **SIS multilayers**
- **Cu (interdiffusion studies)**

# Conclusion

Positron Annihilation Spectroscopy

# Conclusion

## Positron Annihilation Spectroscopy

- **non-destructive** characterization of defects
- vacancy-like defects **down to atomic scale**
- **depth profiling**
- combination with **ATSUP** calculations
  
- Doppler-Broadening-Spectroscopy (**DBS**)
  - **defect concentration & atomic environment** of defects
  
- Positron Annihilation Lifetime Spectroscopy (**PALS**)
  - **defect typ, size & density**

# Acknowledgement

Contact:  
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***THANK YOU FOR  
YOUR ATTENTION !***



ELBE as user facility!

## Institute of Radiation Physics, HZDR, Germany

- Dr. Andreas Wagner
  - Dr. Maciej Oskar Liedke
  - Dr. Ahmed Gamal Attallah Elsherif
  - Dr. Maik Butterling
  - Dr. Eric Hirschmann
- and more...

## Institute of Materials Engineering, University of Siegen, Germany

- Prof. Dr. rer. nat. habil. Xin Jiang
  - Dr. Aleksandr Zubtsovskii
  - M.Sc. Bharath Reddy Lakki Reddy Venkata
- and more...